

Features

- Low drain-source on-resistance: $R_{DS(ON)}=0.18\Omega(\text{typ})$
- Easy to control gate switching
- Enhancement mode: $V_{th} = 2.0$ to $4.0V$
- 100% avalanche tested
- Built-in ESD Diode
- RoHS compliant

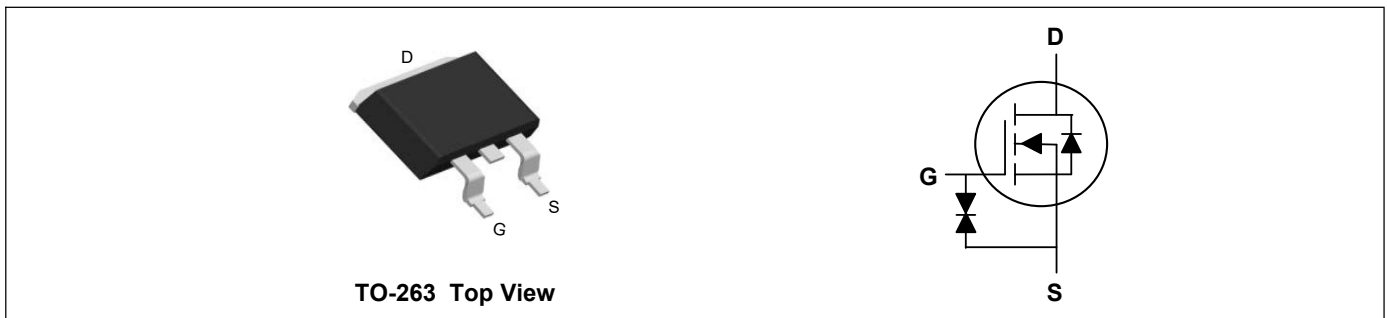
Key Performance Parameters



Parameter	Value	Unit
$V_{DS} @ T_{j,max}$	650	V
$R_{DS(ON),max}$	210	m Ω
I_D	16.8	A
$Q_{g,typ}$	40	nC
I_{DM}	50	A

Applications

- Switch Mode Power Supply (SMPS)
- TV power & LED Lighting Power
- AC to DC Converters
- Telecom



Absolute Maximum Ratings($T_C=25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	650	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ¹	$I_D @ T_C=25^\circ\text{C}$	16.8	A
Continuous Drain Current ¹	$I_D @ T_C=100^\circ\text{C}$	10.6	A
Pulsed Drain Current ²	I_{DM}	50	A
Single Pulse Avalanche Energy ⁴	EAS	250	mJ
Avalanche Current	I_{AS}	2.4	A
MOSFET dv/dt ruggedness, $V_{DS} = 0 \dots 400V$	dv/dt	50	V/ns
Reverse diode dv/dt ³ $V_{DS}=0 \dots 400V, I_{SD} \leq I_D$		15	
Total Power Dissipation ($T_C=25^\circ\text{C}$)	P_D	105	W
Gate source ESD(HBM-C=100pF, R=1.5K Ω)	$V_{ESD(G-S)}$	2000	V
Storage Temperature Range	T_{STG}	-55 to 150	$^\circ\text{C}$
Operating Junction Temperature Range	T_J	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance Junction-Ambient (Max)	$R_{\theta JA}$	62	$^\circ\text{C/W}$
Thermal Resistance Junction-Case (Max)	$R_{\theta JC}$	1.2	$^\circ\text{C/W}$

Electrical Characteristics (T_J=25°C, unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =1mA	650	---	---	V
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =6.2A	---	180	210	mΩ
Gate Threshold Voltage	V _{GS(th)}	V _{GS} =V _{DS} , I _D =670uA	2.0	---	4.0	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =650V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =650V, V _{GS} =0V, T _J =150°C	---	---	100	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	---	---	±1	uA
Total Gate Charge	Q _g	V _{DD} =520V, V _{GS} =10V, I _D =8.7A	---	40	---	nC
Gate-Source Charge	Q _{gs}		---	8	---	
Gate-Drain Charge	Q _{gd}		---	12	---	
Turn-On Delay Time	T _{d(on)}	V _{DD} =325V, R _G =25Ω, I _D =8.7A	---	39	---	ns
Rise Time	T _r		---	21	---	
Turn-Off Delay Time	T _{d(off)}		---	171	---	
Fall Time	T _f		---	18	---	
Input Capacitance	C _{iss}	V _{DS} =400V, V _{GS} =0V, f=1MHz	---	1750	---	pF
Output Capacitance	C _{oss}		---	39	---	
Reverse Transfer Capacitance	C _{rss}		---	3.4	---	

Drain-Source Diode Characteristics

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Continuous Source Current	I _S	T _C =25°C	---	---	16.8	A
Pulsed Source Current	I _{SM}		---	---	50	A
Diode Forward Voltage	V _{SD}	V _G =0V, I _S =8.7A, T _J =25°C	---	---	1.3	V
Reverse Recovery Time	t _{rr}	V _R =400V, I _F =8.7 A, di _F /dt=100A/μs	---	340	---	ns
Reverse Recovery Charge	Q _{rr}		---	4.7	---	uC

Note:

- Limited by T_{J,max}. Maximum Duty Cycle D = 0.50
- Pulse width t_p limited by T_{J,max}
- Identical low side and high side switch with identical R_θ
- V_{DD}=50V, R_G=25Ω, I_{AS}=2.4A

Typical Characteristics

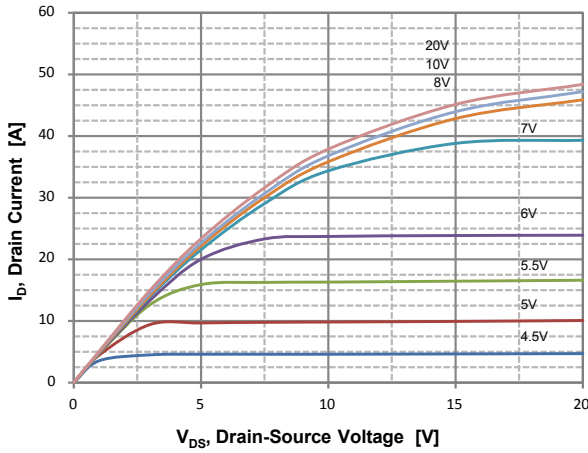


Figure 1. On Region Characteristics

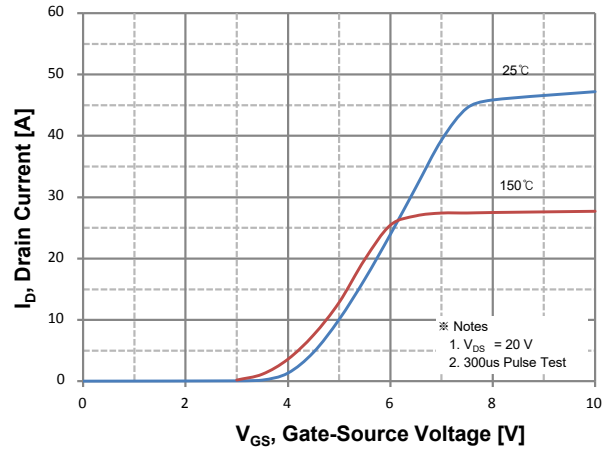


Figure 2. Transfer Characteristics

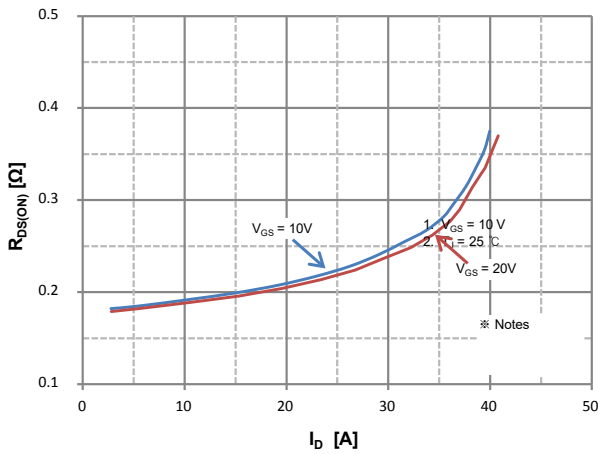


Figure 3. On Resistance Variation vs Drain Current and Gate Voltage

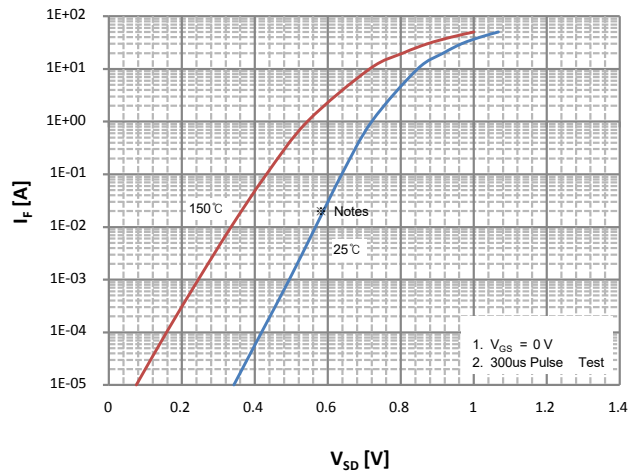


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

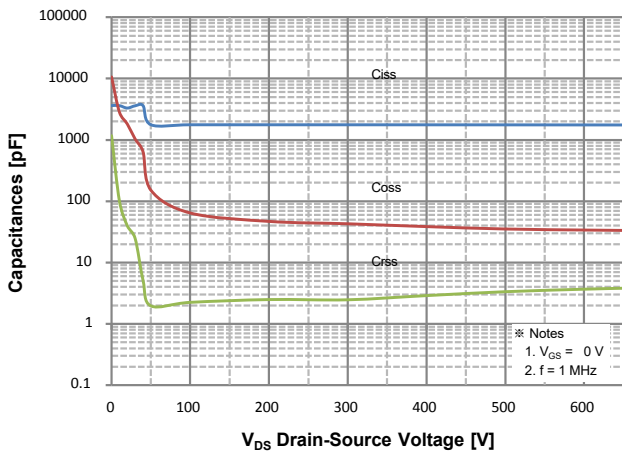


Figure 5. Capacitance Characteristics

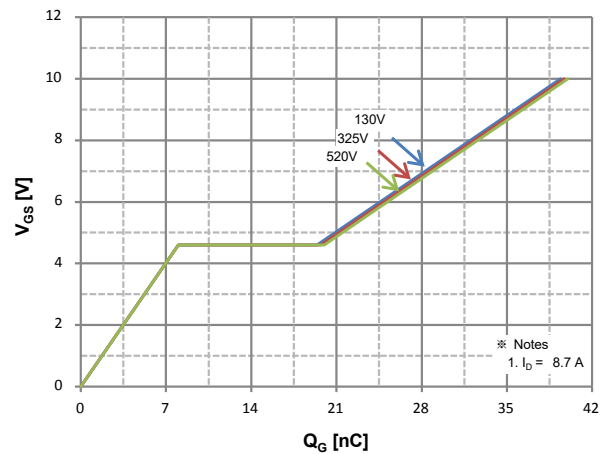


Figure 6. Gate Charge Characteristics

650V Super Junction Power MOSFET

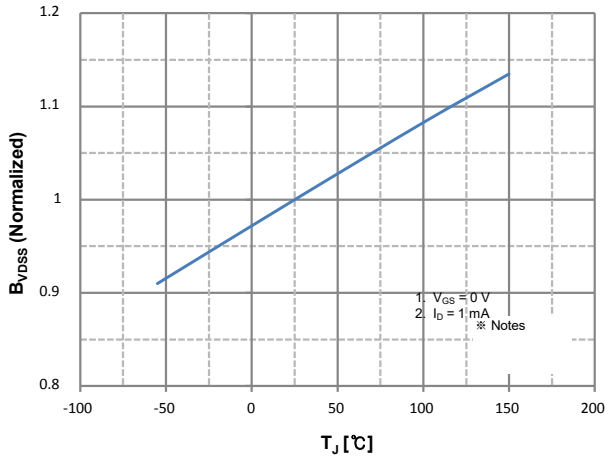


Figure 7. Breakdown Voltage Variation vs. Temperature

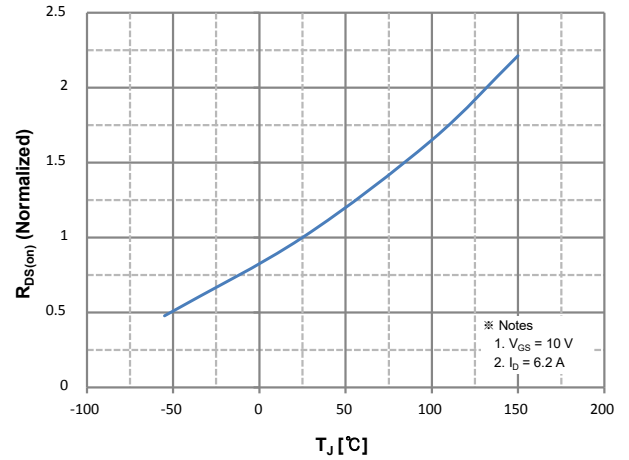


Figure 8. On-Resistance Variation vs. Temperature

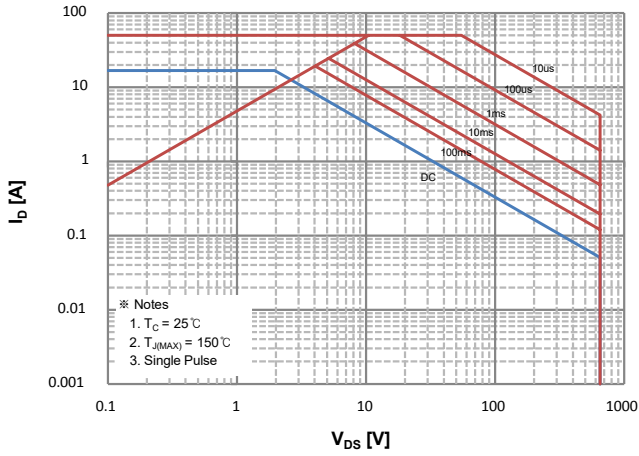


Figure 9. Maximum Safe Operating Area

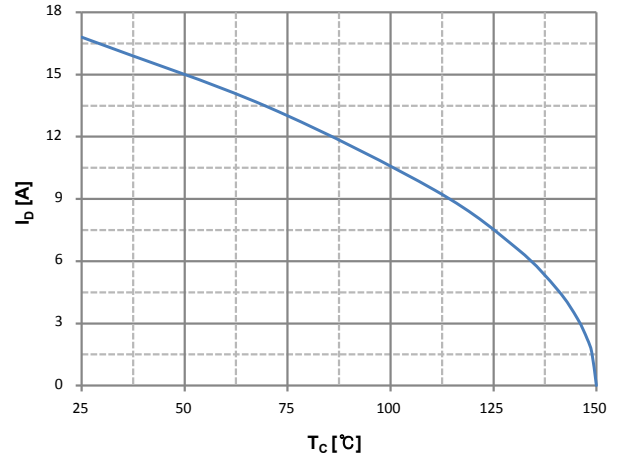


Figure 10. Maximum Drain Current vs. Case Temperature

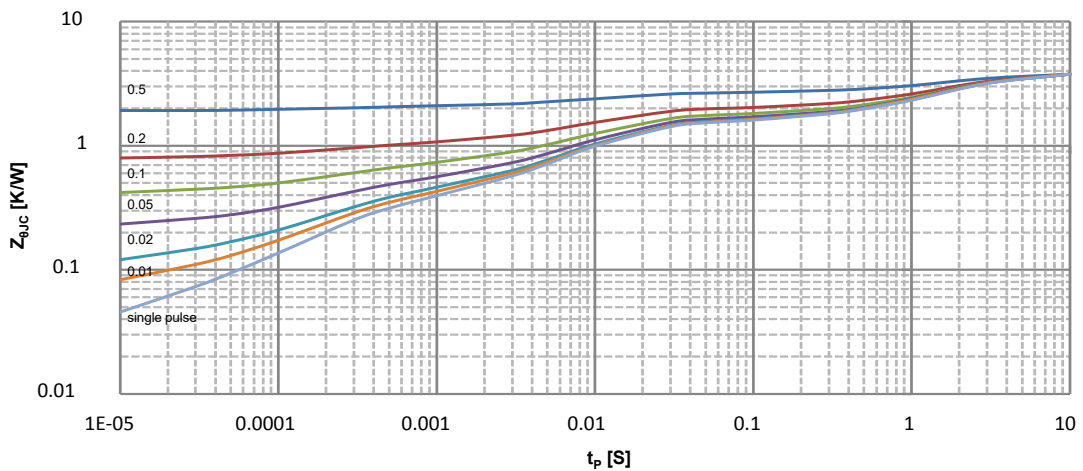
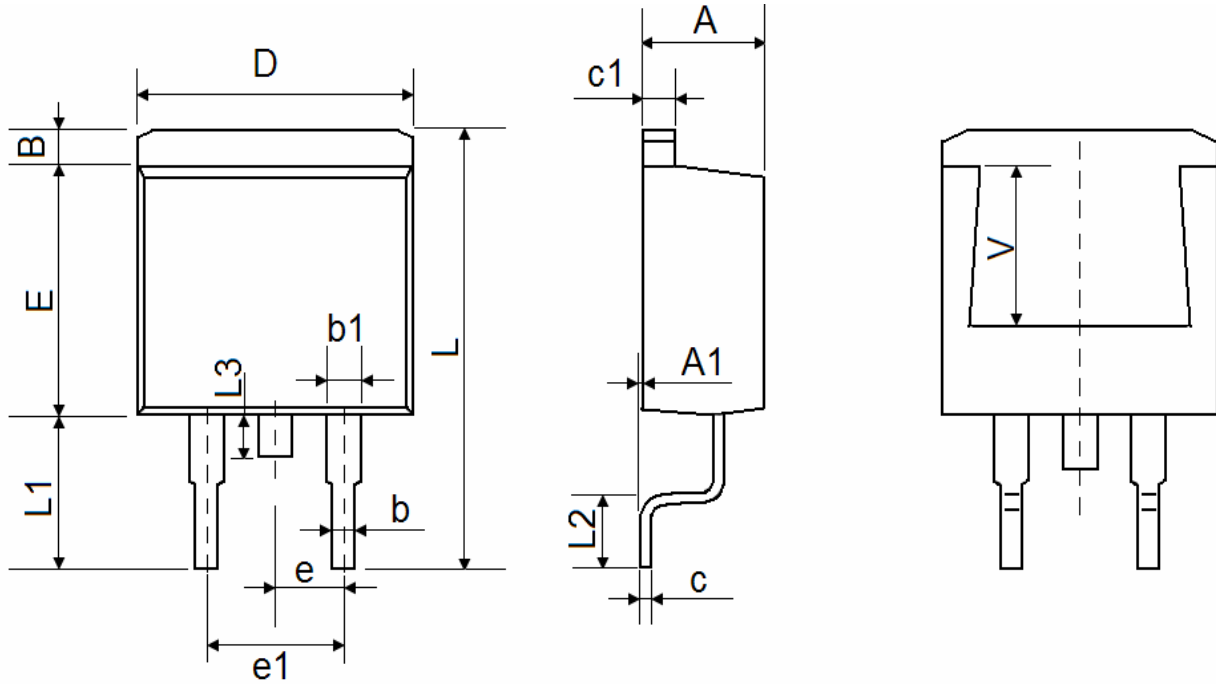


Figure 11. Transient Thermal Response Curve

TO-263 Package Outline Dimensions



Symbol	Dimensions (unit:mm)			Symbol	Dimensions (unit:mm)		
	Min	Typ	Max		Min	Typ	Max
A	4.40	4.55	4.70	A1	0.00	0.07	0.15
B	1.00	1.20	1.40	b	0.65	0.80	0.95
b1	1.10	1.15	1.37	c	0.30	0.40	0.53
c1	1.10	1.25	1.37	D	9.80	10.00	10.40
E	8.50	8.80	9.20	e	2.54 REF		
e1	4.90	5.10	5.40	L	14.80	15.20	15.70
L1	5.00	5.25	5.60	L2	2.05	2.45	2.80
L3	1.20	1.50	1.80	V	5.60 REF		